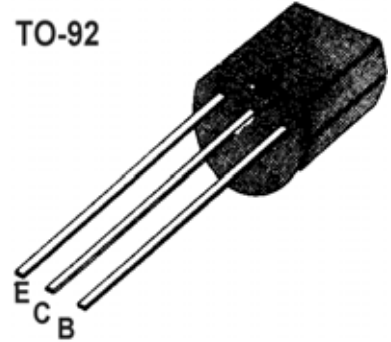


■■ APPLICATION: High Current Application.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-35	V
Collector-emitter voltage	V _{CEO}	-30	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-800	mA
Collector Power Dissipation	P _C	-625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h _{FE}	100		320		V _{CE} = -1V, I _C = -100mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -35V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-35			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-30			V	I _C = -10mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _C =0
Base-Emitter Voltage	V _{BE}	-0.5		-0.8	V	V _{CE} = -1V, I _C = -10mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.7	V	I _C = -500mA, I _B = -20mA
Gain bandwidth product	f _T		120		MHz	I _C = -10mA, V _{CE} = -5V
Common Base Output Capacitance	C _{ob}		19		PF	V _{CB} = -10V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification	O	Y
h _{FE}	100~200	160~320